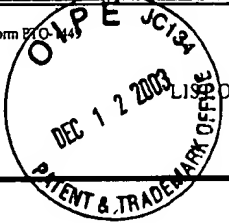


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<div style="text-align: center;">  </div>				LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)			
				APPLICANT Klaus Florian Schuegraf et al.			
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U.S. PATENT DOCUMENTS							
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OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)							
EO	AC	1	Ohnishi, K. et al., <i>Improving Gate Oxide Integrity (GOI) of a W1Wx1 dual-poly Si Stacked-Gate by Using Wet-Hydrogen Oxidation in 0.14-<math>\mu</math>m CMOS Devices</i> , IEEE, 1998, pgs. 397-400.				
EO	AD	1	Kawada, K. et al., <i>Water Vapor Generator By Catalytic Reactor</i> , pgs. 10-16.				
EO	AE	1	Wakabayashi, H. et al., <i>An Ultra-Low Resistance and Thermally Stable W1pn-Poly-Si Gate CMOS Technology using SiTiN Buffer Layer</i> , IEEE, 1998, pgs. 393-396.				
EO	AF	1	Hiura, Y. et al., <i>Integration Technology of Polymetal (W1W5SiN/Poly-Si) Dual Gate CMOS for 1 Gbit DRAMs and Beyond</i> , IEEE, 1998, pgs. 389-392.				
EO	AG	1	Nagahama, T. et al., <i>Wet Hydrogen Oxidation System for Metal Gate LSI's</i> , pgs. 140-143				
EO	AH	1	Lee, B. et al., <i>In-situ Barrier Formation for High Reliable W1barrier/poly-Si Gate Using Denudation of WN<sub>x</sub> on Polycrystalline Si</i> , IEEE, 1998, pgs. 385-389.				
<i>Edgardo Lity</i>				3/			
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